

SEMICONDUCTOR DIODES WITH FIN STRUCTURE

ABSTRACT OF THE DISCLOSURE

A semiconductor diode structure is provided which includes a substrate; a fin formed of a semiconducting material positioned vertically on the substrate, the fin includes a first
5 heavily-doped region of a first doping type on one side and a second heavily-doped region of a second doping type on an opposite side; and a first conductor contacting the first heavily-doped region and a second conductor contacting the second heavily-doped region.

FIG. 2B